

Silicon PNP Power Transistors

2N5867 2N5868

DESCRIPTION

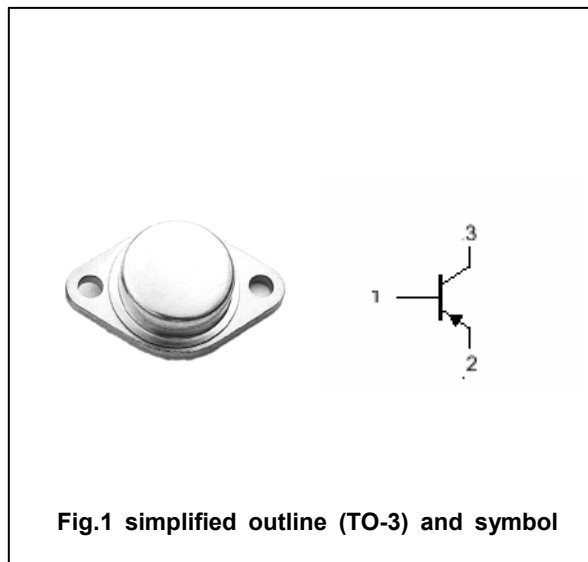
- With TO-3 package
- Low collector saturation voltage

APPLICATIONS

- For medium-speed switching and amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N5867	Open emitter	-60	V
		2N5868		-80	
V_{CEO}	Collector-emitter voltage	2N5867	Open base	-60	V
		2N5868		-80	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-5	A
P_D	Total Power Dissipation		$T_C = 25\square$	87.5	W
T_j	Junction temperature			150	$\square$
T_{stg}	Storage temperature			-65~200	$\square$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	1.17	$\square/W$

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CHARACTERISTICS

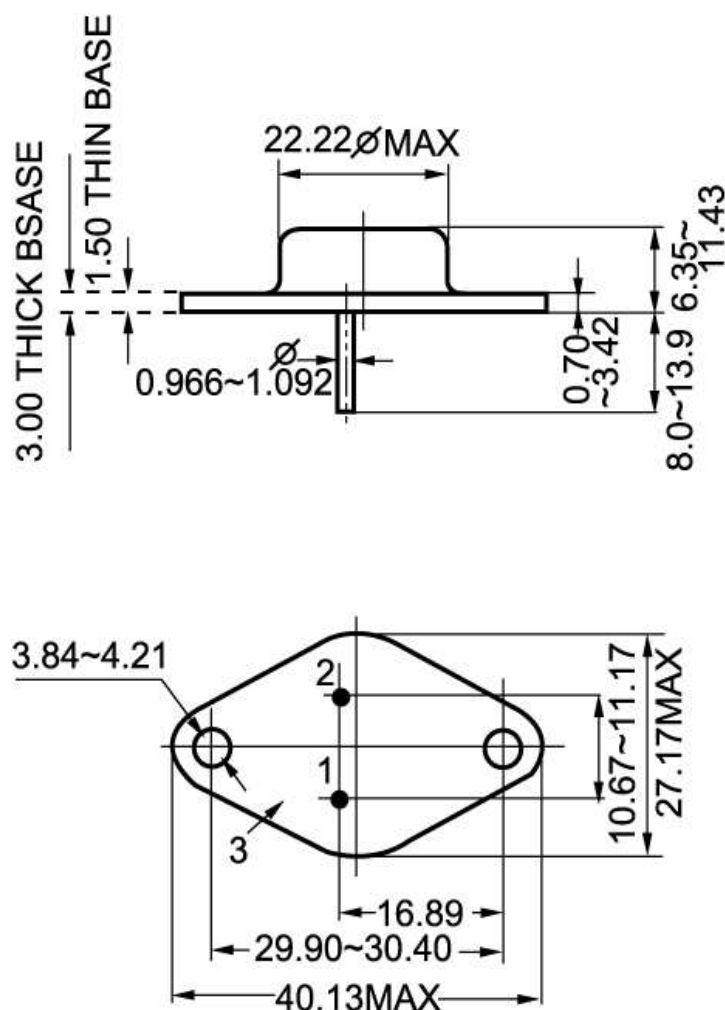
T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N5867	I _C =-0.1A; I _B =0	-60			V
		2N5868		-80			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-5A; I _B =-1A			-1.0	V
V _{BEsat}	Base-emitter saturation voltage		I _C =-5A; I _B =-1A			-1.5	V
I _{CBO}	Collector cut-off current		V _{CB} =rated V _{CBO} ; I _B =0			-1.0	mA
I _{CEO}	Collector cut-off current	2N5867	V _{CE} =-30V; I _B =0			-2.0	mA
		2N5868	V _{CE} =-40V; I _B =0				
I _{EBO}	Emitter cut-off current		V _{EB} =-5V; I _C =0			-1.0	mA
h _{FE}	DC current gain		I _C =-1.5A; V _{CE} =-4V	20		100	
f _T	Transistion frequency		I _C =-0.5A; V _{CE} =-10V; f=1MHz	4			MHz

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PACKAGE OUTLINE

Fig.2 outline dimensions (unindicated tolerance: $\pm 0.10\text{mm}$)